100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
100V	15mΩ @ V_{GS} = 10V	34A
	19.5mΩ @ V_{GS} = 6V	32A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

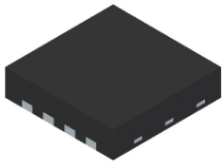
Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and Loadswitch..

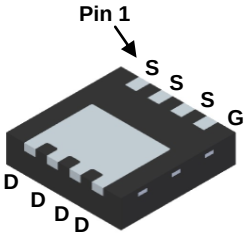
- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

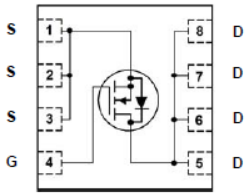
- Case: V-DFN3333-8 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (Approximate)



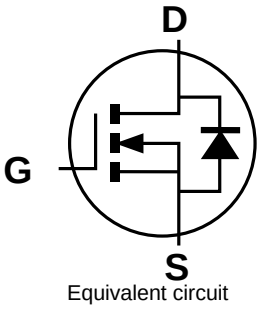
Top View



Bottom View



Top View
Internal Schematic



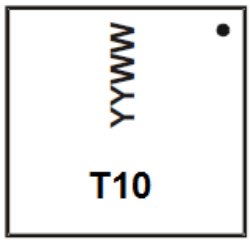
Equivalent circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H015LCG-7	V-DFN3333-8 (Type B)	2,000/Tape & Reel
DMT10H015LCG-13	V-DFN3333-8 (Type B)	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T10 = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 6)	Steady State	T_A = +25°C T_A = +70°C	I_D	9.4 7.5	A
Continuous Drain Current, V_{GS} = 10V	Steady State	T_C = +25°C T_C = +100°C	I_D	34 21	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.6	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	54	A
Avalanche Current, L = 3mH (Note 8)			I_{AS}	7.5	A
Avalanche Energy, L = 3mH (Note 8)			E_{AS}	85	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	118	°C/W
Total Power Dissipation (Note 6)	P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	59	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.5	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	2	3.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	12.1	15	mΩ	V_{GS} = 10V, I_D = 20A
		—	15	19.5		V_{GS} = 6V, I_D = 20A
		—	18.9	26	mΩ	V_{GS} = 4.5V, I_D = 5A
Diode Forward Voltage	V_{SD}	—	0.9	1.3	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1871	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	261	—		
Reverse Transfer Capacitance	C_{rss}	—	6.9	—		
Gate Resistance	R_g	—	0.75	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	33.3	—	nC	V_{DD} = 50V, I_D = 10A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	6.9	—		
Gate-Drain Charge	Q_{gd}	—	5.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.5	—	ns	V_{DD} = 50V, V_{GS} = 10V, I_D = 10A, R_g = 6Ω
Turn-On Rise Time	t_R	—	7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	19.7	—		
Turn-Off Fall Time	t_F	—	8.1	—		
Reverse Recovery Time	t_{RR}	—	37.9	—	ns	I_F = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	51.9	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

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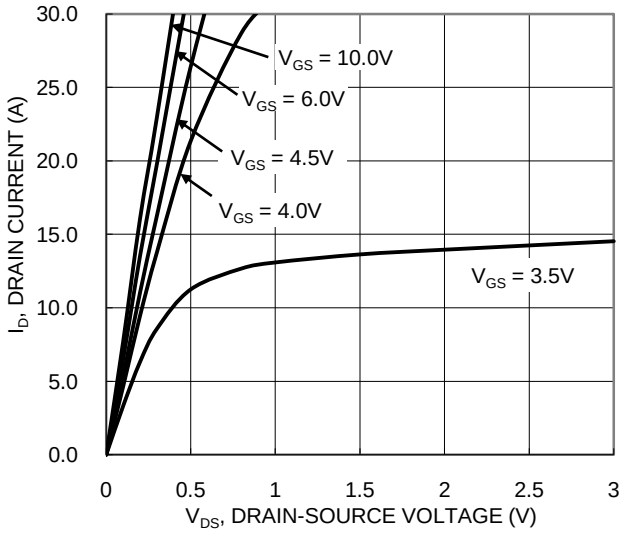

Figure 1. Typical Output Characteristic

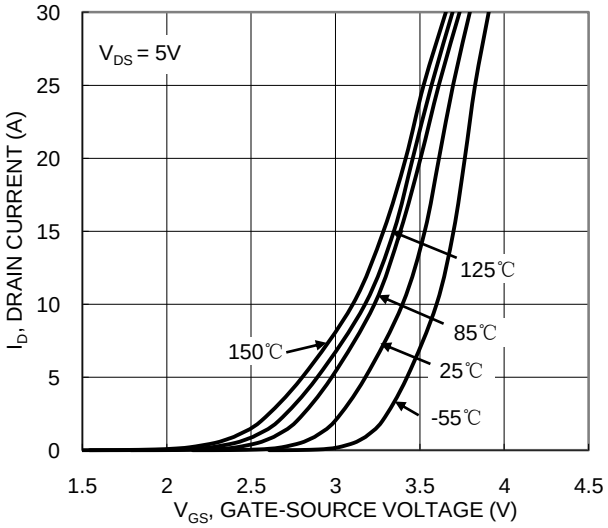

Figure 2. Typical Transfer Characteristic

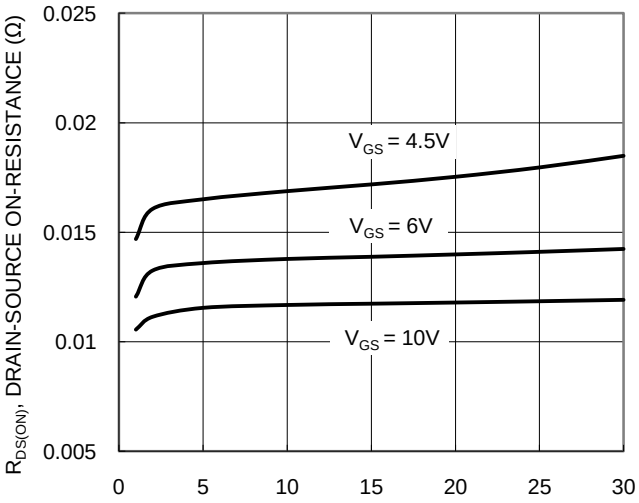

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

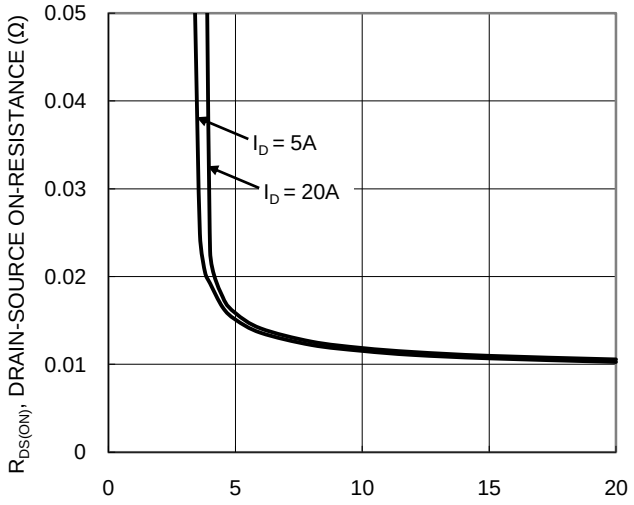

Figure 4. Typical Transfer Characteristic

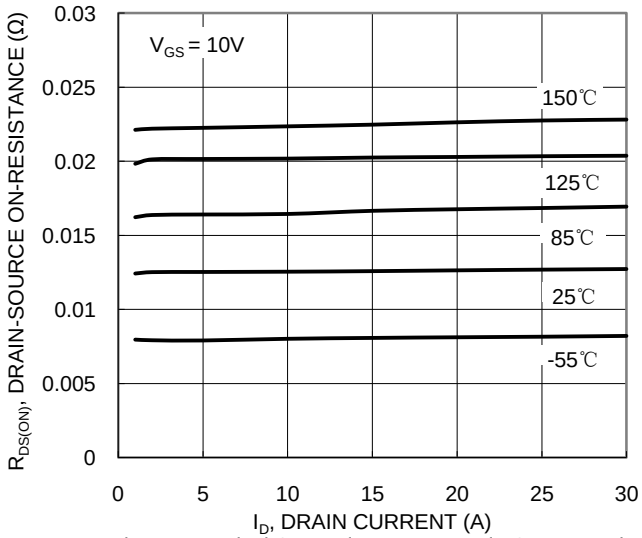

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

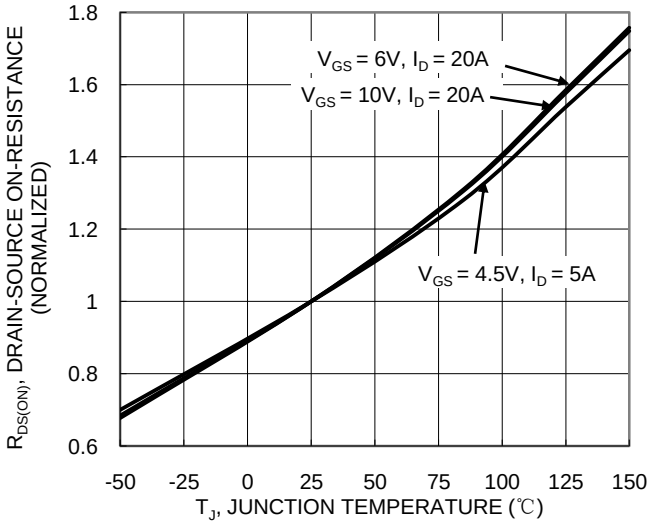

Figure 6. On-Resistance Variation with Junction Temperature

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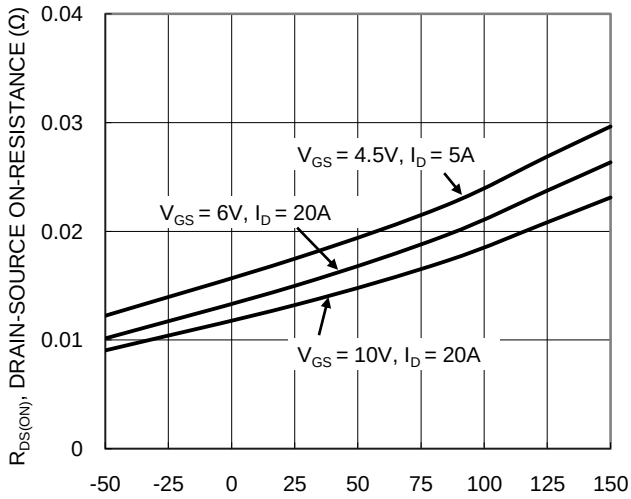

Figure 7. On-Resistance Variation with Junction Temperature

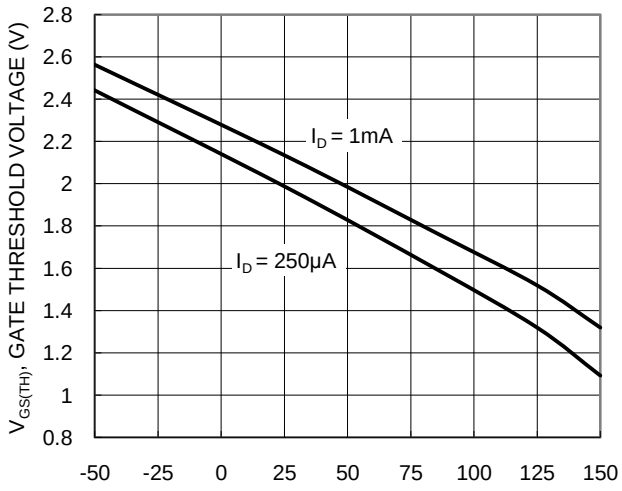

Figure 8. Gate Threshold Variation vs. Junction Temperature

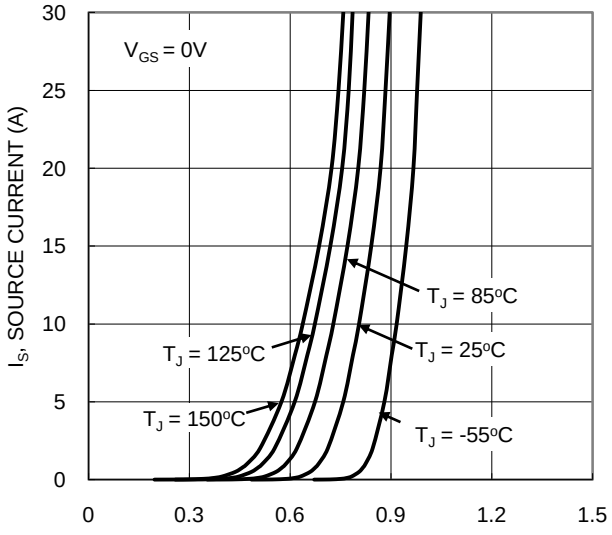

Figure 9. Diode Forward Voltage vs. Current

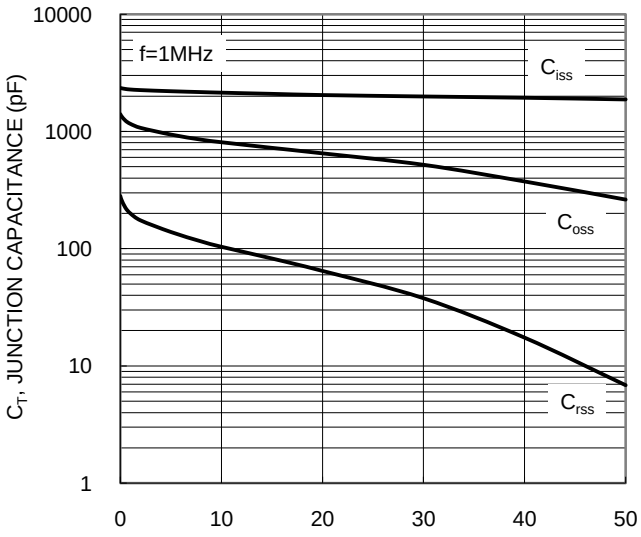

Figure 10. Typical Junction Capacitance

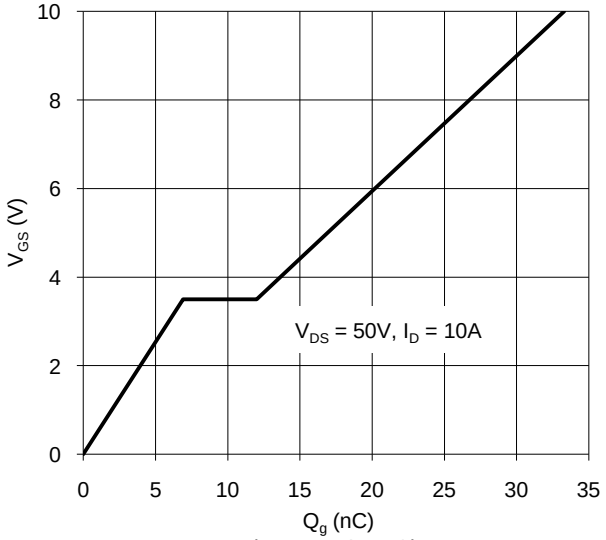

Figure 11. Gate Charge

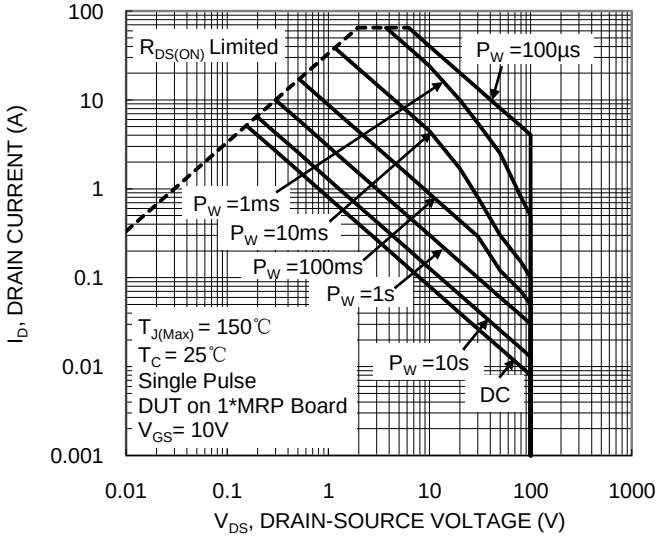

Figure 12. SOA, Safe Operation Area

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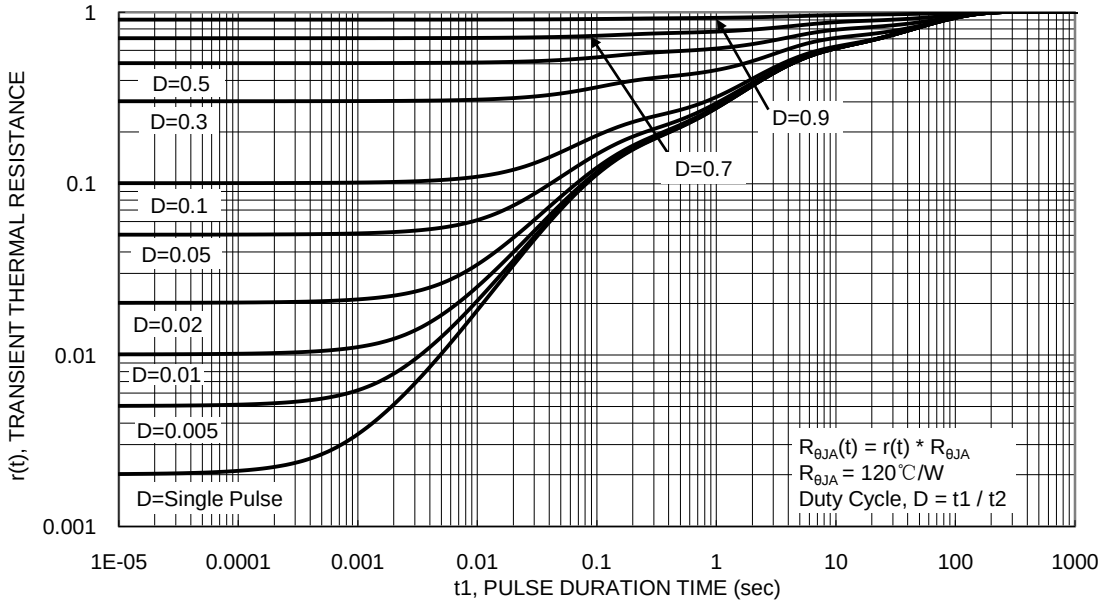

Figure 13. Transient Thermal Resistance

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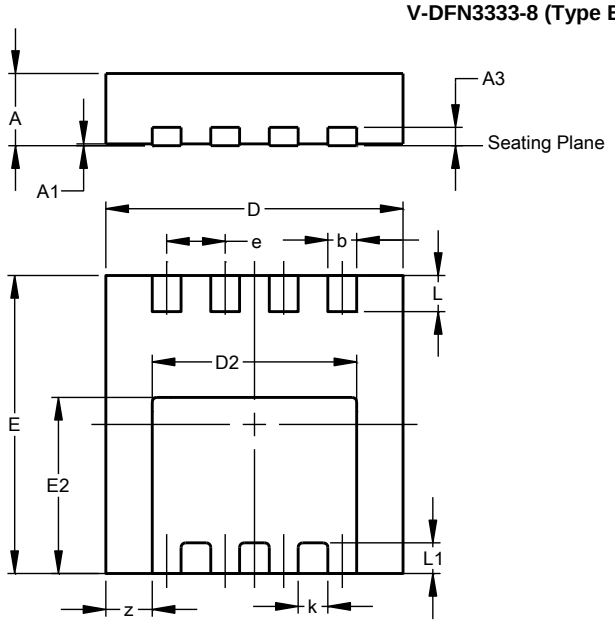
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-DFN3333-8 (Type B)

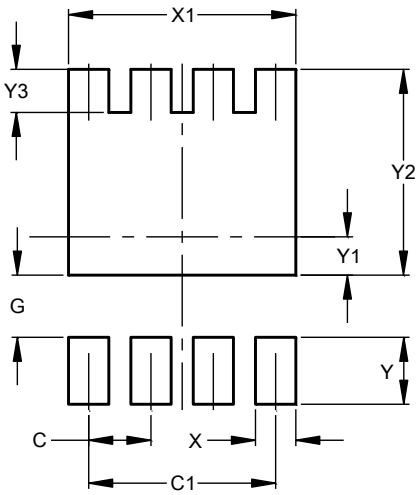


V-DFN3333-8 (Type B)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.27	0.37	0.32
D	3.25	3.35	3.30
D2	2.17	2.37	2.27
E	3.25	3.35	3.30
E2	1.85	2.05	1.95
e	--	--	0.65
k	--	--	0.33
L	0.35	0.45	0.40
L1	--	--	0.34
z	--	--	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-DFN3333-8 (Type B)



Dimensions	Value (in mm)
C	0.650
C1	1.950
G	0.650
X	0.420
X1	2.370
Y	0.700
Y1	0.400
Y2	2.150
Y3	0.450

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